NSN 5961-01-034-4950

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View Online at https://aerobasegroup.com/nsn/5961-01-034-4950 **Inclosure Material:** Metal **Overall Length:** 1.330 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Internal Junction Configuration:** Npn **Component Function Relationship:** Matched **Component Name And Quantity:** 4 transistor **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.667 inches and 0.687 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 275.0 collector to base voltage/static/emitter open and 250.0 collector to emitter voltage/static/base open and 6.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 30.00 amperes source cutoff current **Power Rating Per Characteristic:** 175.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:**

200.0 degrees celsius ambient air

Special Features:

Matched set of 4 transistors; matched to within 200 mv maximum vce; matched to within 20% of the mean beta for that group of 4

Test Data Document:

34217-6020028 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unf

Terminal Type And Quantity:

3 tab, solder lug

Shelf Life:

N/a

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In	18	<i>(</i>)+	МЛО	201	ure:

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Demilitarization:

No

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